

MASK CORRECTION FOR PHOTOLITHOGRAPHIC PROCESSES

ABSTRACT OF THE DISCLOSURE

Local images of photolithographic masks are
5 assigned to classes based on similarity of functions
of circuits formed by the images, so that all of the
images of a class can be corrected by correcting one
of the members. Boundaries of photolithographic
masks are corrected for diffusion of light by moving
10 regions based on process light intensity and
proximity of close connections. Boundaries are also
corrected for shifting of photoactive material in
photoresists by calculating the amount of shift based
on light intensities at pattern points.

15